Elektronische Bauelemente

SCS70DSTL-C

0.075A , 85V

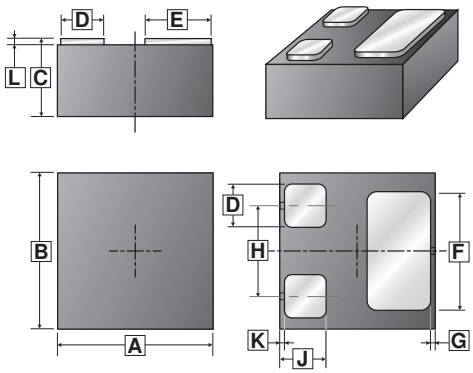
Plastic-Encapsulated Switching Diode

RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

DESCRIPTION

- Epitaxial Planar Silicon Diode

WBFBP-03D



FEATURES

- Fast Switching Speed
- Ultra-Small Surface Mount Package
- For General Purpose Switching Applications
- High Conductance

APPLICATIONS

- For General Purpose Switching Applications, Rectifiers
- For Portable Equipment: (i.e. Mobile phone, MP3, MD, CD-ROM, DVD-ROM, Note book PC, etc.)

MARKING

JJ

REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	0.950	1.050	G	-	0.050
B	0.950	1.050	H	0.510	0.610
C	0.010	0.070	J	0.250	0.350
D	0.210	0.310	K	-	0.050
E	0.350 REF.		L	0.450	0.550
F	0.680 REF.				

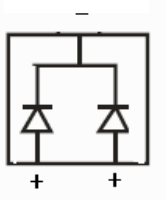
PACKAGE INFORMATION

Package	MPQ	Leader Size
WBFBP-03D	5K	7 inch

ORDER INFORMATION

Part Number	Type
SCS70DSTL-C	Lead (Pb)-free and Halogen-free

TOP VIEW



ABSOLUTE MAXIMUM RATINGS (T_A=25℃ unless otherwise specified)

Parameters	Symbol	Ratings	Unit
DC Blocking Voltage	V_R	85	V
Average Rectified Output Current	I_O	75	mA
Power Dissipation	P_D	100	mW
Operating Junction and Storage Temperature	T_J, T_{STG}	150, -55~150	℃

ELECTRICAL CHARACTERISTICS (T_A=25℃ unless otherwise specified)

Parameters	Symbol	Min.	Max.	Unit	Test Conditions
Reverse Breakdown Voltage	$V_{(BR)}$	85	-	V	I_R=100μA
Maximum DC Reverse Current @Rated DC Blocking Voltage	I_{R1}	-	2	μA	V_R=75V
	I_{R2}	-	0.03	μA	V_R=25V
Forward Voltage	V_{F1}	-	0.715	V	I_F=1mA
	V_{F2}	-	0.855	V	I_F=10mA
	V_{F3}	-	1	V	I_F=50mA
	V_{F4}	-	1.25	V	I_F=150mA
Diode Capacitance	C_D	-	1.5	pF	V_R=0, f=1MHz
Maximum Reverse Recovery Time	T_{RR}	-	4	nS	I_F=I_R=10mA Irr=0.1XI_R, R_L=100Ω

CHARACTERISTIC CURVES

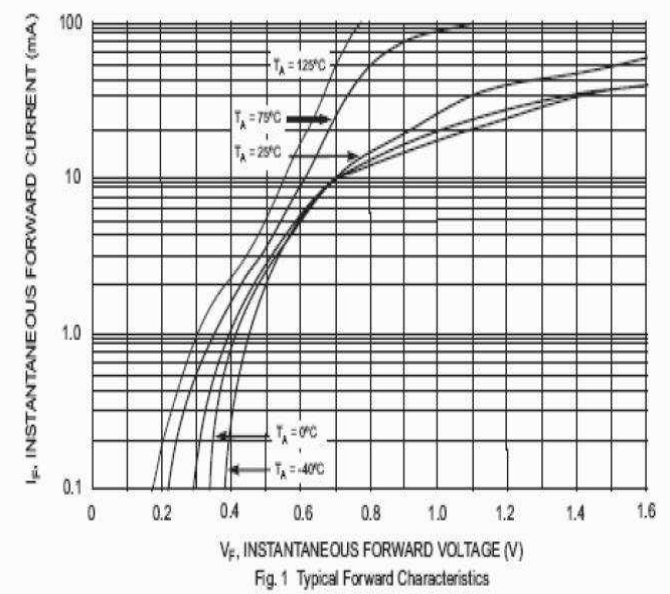


Fig. 1 Typical Forward Characteristics

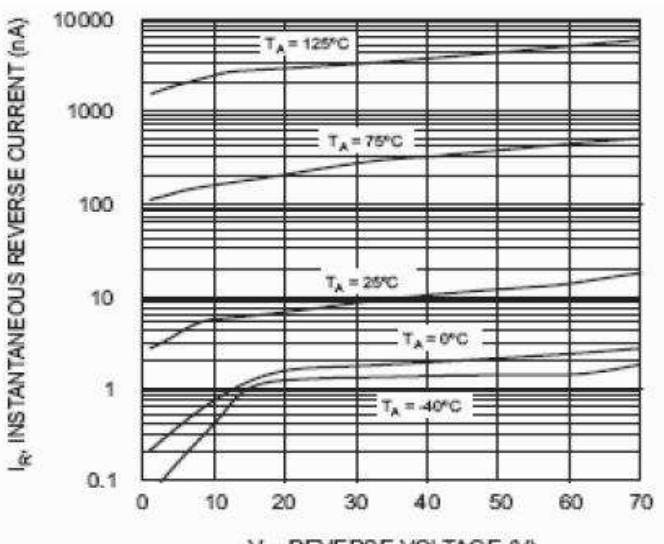


Fig. 2 Typical Reverse Characteristics

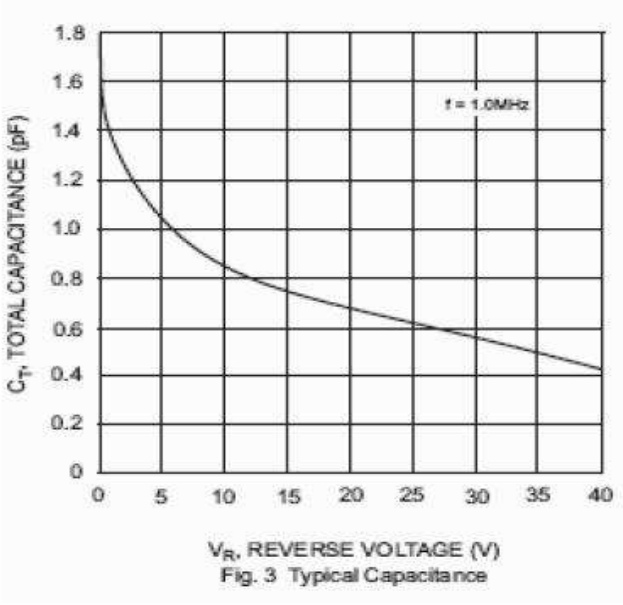


Fig. 3 Typical Capacitance

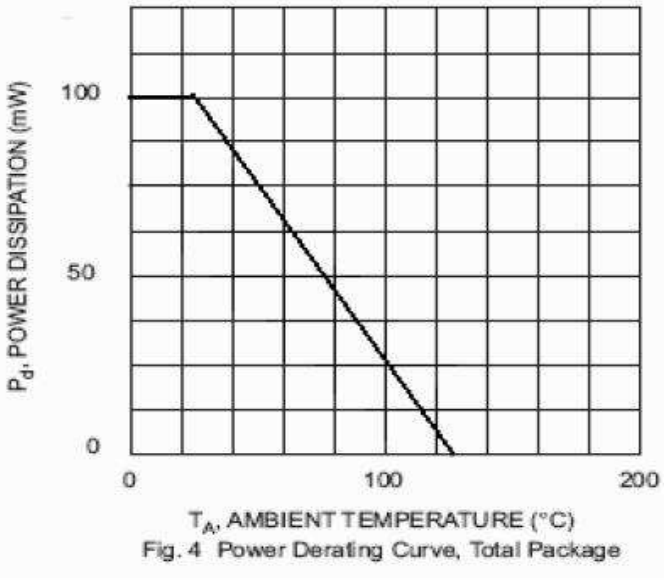


Fig. 4 Power Derating Curve, Total Package